



- (51) International Patent Classification: Not classified
- (21) International Application Number:
PCT/US2012/044581
- (22) International Filing Date:
28 June 2012 (28.06.2012)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
13/175,482 1 July 2011 (01.07.2011) US
- (71) Applicant (for all designated States except US): **MI-CRON TECHNOLOGY, INC.** [US/US]; 8000 S Federal Way, Boise, Idaho 83716-9632 (US).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): **SILLS, Scott E.** [US/US]; 1316 S Gourley Street, Boise, Idaho 83705 (US).
- (74) Agent: **KERN, Jacob T.**; Brooks, Cameron & Huebsch, PLLC, 1221 Nicollet Avenue, Suite 500, Minneapolis, Minnesota 55403 (US).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM,

AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished upon receipt of that report (Rule 48.2(g))

(54) Title: MEMORY CELL STRUCTURES

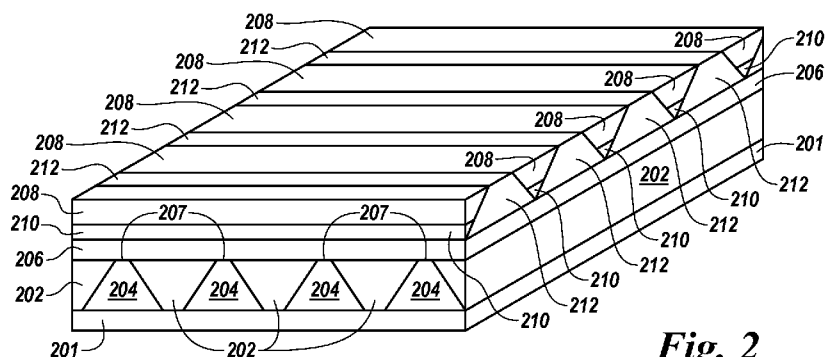


Fig. 2

(57) Abstract: The present disclosure includes memory cell structures and method of forming the same. One such memory cell includes a first electrode having sidewalls angled less than 90 degrees in relation to a bottom surface of the first electrode, a second electrode, including an electrode contact portion of the second electrode, having sidewalls angled less than 90 degrees in relation to the bottom surface of the first electrode, wherein the second electrode is over the first electrode, and a storage element between the first electrode and the electrode contact portion of the second electrode.